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Declarations under Rule 4.17:

— as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))

[Continued on next page]

(54) Title: THROUGH SILICON VIA BRIDGE INTERCONNECT

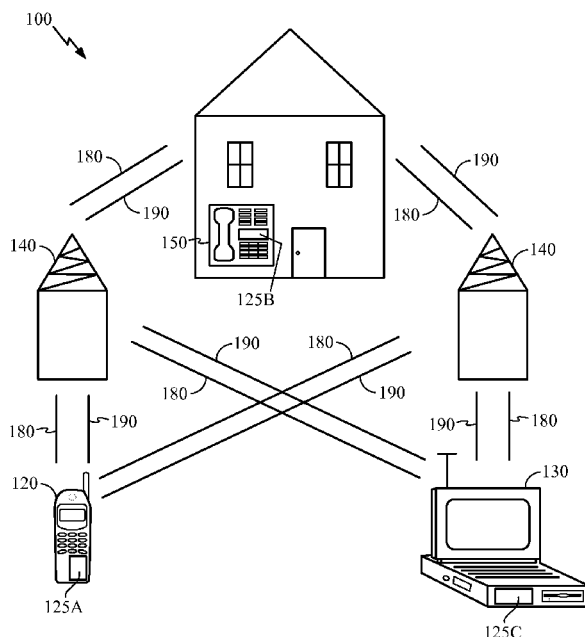


FIG. 1

(57) Abstract: An integrated circuit bridge interconnect system includes a first die and a second die provided in a side by side configuration and electrically interconnected to each other by a bridge die. The bridge die includes through silicon vias (TSVs) to connect conductive interconnect lines on the bridge die to the first die and the second die. Active circuitry, other than interconnect lines, may be provided on the bridge die. At least one or more additional die may be stacked on the bridge die and interconnected to the bridge die.



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- *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))* — *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*

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